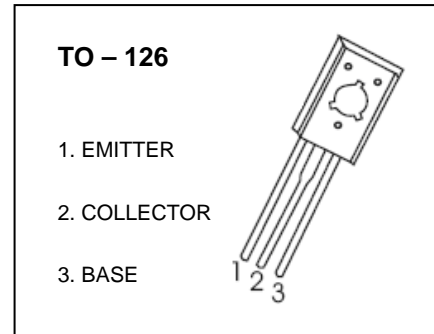
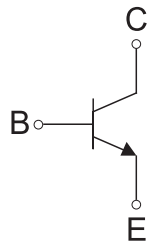


2SD2136 TRANSISTOR (NPN)

FEATURES

- High Forward Current Transfer Ratio h_{FE} Which has Satisfactory Linearity.
- Low Collector-Emitter Saturation Voltage $V_{CE(sat)}$
- Allowing Supply with the Radial Taping

Equivalent Circuit



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	3	A
P_C	Collector Power Dissipation	1.25	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	100	$^{\circ}\text{C/W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

$T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}^*$	$I_C=30\text{mA}, I_B=0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}, I_E=0$			200	μA
Collector cut-off current	I_{CEO}	$V_{CE}=60\text{V}, I_B=0$			300	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6\text{V}, I_C=0$			1	mA
DC current gain	$h_{FE(1)}^*$	$V_{CE}=4\text{V}, I_C=1\text{A}$	40		250	
	$h_{FE(2)}^*$	$V_{CE}=4\text{V}, I_C=3\text{A}$	10			
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	$I_C=3\text{A}, I_B=0.375\text{A}$			1.2	V
Base-emitter voltage	V_{BE}^*	$V_{CE}=4\text{V}, I_C=3\text{A}$			1.8	V
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=0.1\text{A}, f=10\text{MHz}$		30		MHz

*Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2.0\%$.

CLASSIFICATION OF $h_{FE(1)}$

RANK	P	Q	R
RANGE	40-90	70-150	120-250

